Octal D Flip-Flop with Common Clock and Enable

High-Performance Silicon-Gate CMOS

The MC74HC377A is identical in pinout to the LS273. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of eight D flip-flops with common Clock and Enable (E) inputs. Each flip-flop is loaded with a low-to-high transition of the Clock input. Enable (\overline{E}) is active low.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 264 FETs or 66 Equivalent Gates
- These are Pb-Free Devices



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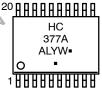
MARKING DIAGRAMS







TSSOP-20 DT SUFFIX CASE 948E



Assembly Location

Wafer Lot YY, Y = Year WW. W = Work Week = Pb-Free Package = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

Ē	1●	20	v _{cc}
Q0 [2	19] Q7
D0 [3	18	D7
D1 [4	17	D6
Q1 [5	16	Q6
Q2 [6	15	Q5
D2 [7	14	D5
D3 [8	13	D4
Q3 [9	12	Q4
GND [10	11	СГОСК
			-

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

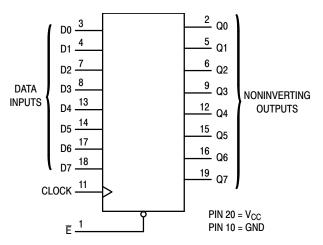


Figure 1. Logic Diagram

FUNCTION TABLE

On a ration or		Outputs		
Operating Modes	Clock	Ē	Dn	Qn
Load "1"	↑	1	h	Н
Load "0"	↑	1	1	L
Hold (Do Nothing)	↑ X	h H	X	No Change No Change

H = HIGH voltage level

h = HIGH voltage level one setup time prior to the LOW-to-

HIGH CP transition

L = LOW voltage level

 $\ensuremath{\mathsf{I}} = \ensuremath{\mathsf{LOW}}$ voltage level one setup time prior to the LOW-to-HIGH CP transition

↑ = LOW-to-HIGH CP transition

X = Don't Care

Design Criteria	Value	Units
Internal Gate Count*	66	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рЈ

*Equivalent to a two-input NAND gate.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC377ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC377ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC377ADTG	TSSOP-20*	75 Units / Rail
MC74HC377ADTR2G	TSSOP-20*	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air SOIC Package [†] TSSOP Package [†]	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

	10001 1 ackage	430		level (e.g., either GND or V _{CC}).
T _{stg}	Storage Temperature	-65 to +150	°C	Unused outputs must be left open.
ratings only Extended of reliability. †Derating	exceeding Maximum Ratings may damage the device. y. Functional operation above the Recommended Operation exposure to stresses above the Recommended Operating - SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C MENDED OPERATING CONDITIONS	ting Conditions is not	implied.	NEW DESIGN
Symbol	Parameter Parameter	Min Max	Unit	NEV
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0 6.0	V	`
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0 V _{CC}	V	semilon
T _A	Operating Temperature, All Package Types	-55 +125	°C	SOLIO
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 2) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 1000 0 500 400	ns-OF	5MI
	Input Rise and Fall Time (Figure 2) VCC = 2.0 V VCC = 4.5 V VCC = 6.0 V	TAUFOR		

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC}	–55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\ I_{out} &\leq 20 \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{in} = V_{IH} & & I_{out} \leq 4.0 \text{ m/s} \\ & I_{out} \leq 5.2 \text{ m/s} \end{aligned} $	4.5 A 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	٧
		$V_{in} = V_{IL}$ $ I_{out} \le 4.0 \text{ m/s}$ $ I_{out} \le 5.2 \text{ m/s}$	4.5 4 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 µA	6.0	4,0	40	160	μΑ
	Maximum Input Leakage Current Maximum Quiescent Supply Current (per Package)	O RECONTACTOR OT RECONTACTOR SENTATIVE FOR	2 INF	ORI			

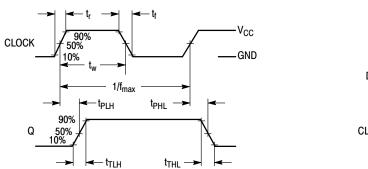
AC Electrical Characteristics (C_L = 50 pF, Input t_r , t_f = 6.0 ns)

				Gua	ranteed Lir	nits	
Symbol	Parameter	Test Conditions	V _{CC} (V)	-55°C to 25°	≤ 85°C	≤ 125°C	Unit
t _{PHL} , t _{PLH}	Maximum Propagation Delay	Figures 2, 4	2.0	160	200	240	ns
	Clock to Qn		4.5	32	40	48	
			6.0	27	34	41	
t _{THL} , t _{TLH}	Maximum Output Transition	Figures 2, 4	2.0	75	95	110	ns
	Time		4.5	15	19	22	
			6.0	13	16	19	
t _W	Minimum Clock Pulse Width	Figure 2	2.0	80	100	120	ns
	High or Low		4.5	16	20	24	
			6.0	4	17	20	
t _{su}	Minimum Set-up Time	Figure 3	2.0	60	75	90	ns
	D _n to Clock		4.5	12	15	18	
			6.0	10	13	15	
t _{su}	Minimum Set-up Time Enable to Clock	Figure 3	2.0	60	75	90	ns
	Lilable to Clock		4.5	12	15	18	
			6.0	10	13	15	
t _h	Minimum Hold Time D _n to Clock	Figure 3	2.0	C3	(/3	3	ns
	D _n to Glock	N/	4.5	3	3	3	
		MEI	6.0	3	3	3	
t _h	Minimum Hold Time Enable to Clock	Figure 3	2.0	4	4	4	ns
	Litable to Clock	, CO, CO, C	4.5	4	4	4	
		Figure 3	6.0	4	4	4	
f _{max}	Maximum Clock Pulse Frequency (50% duty cycle)	Figures 2, 4	2.0	6	5	4	ns
	Tricquericy (50% duty cycle)	CETAI	4.5	30	24	20	
		, AS , MI	6.0	35	28	24	
C _{in}	Maximum Input Capacitance	1,5	-	10	10	10	pF

C _{PD}	Typical @ 25°C, V _{CC} = 5.0 V	pF
(Note 1) Power Dissipation Capacitance	35	

^{1.} C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC} (operating) $\approx C_{PD} \times V_{CC} \times f_{IN} \times N_{SW}$ where N_{SW} = total number of outputs switching and f_{IN} = switching frequency.

SWITCHING WAVEFORMS



DATA t_{su} t_{h} V_{CC} t_{su} V_{CC} t_{su} t_{h} $t_$

Figure 3.

Figure 2.

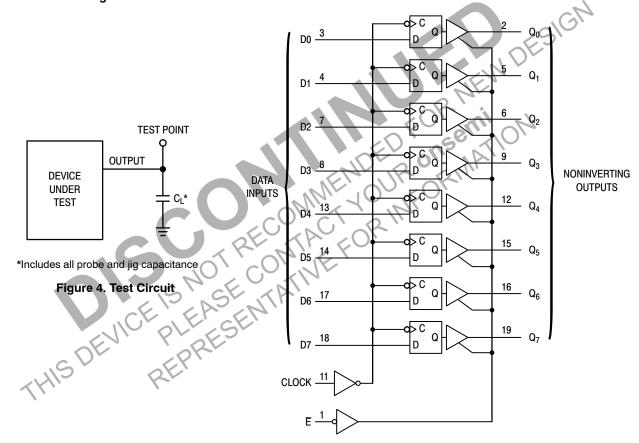


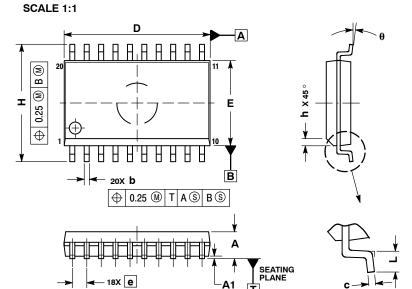
Figure 5. Expanded Logic Diagram





SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

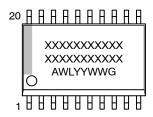
	MILLIMETERS				
DIM	MIN MAX				
Α	2.35	2.65			
A1	0.10	0.25			
b	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0°	7 °			

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

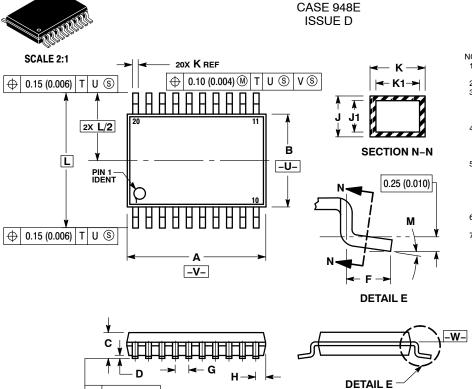
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





TSSOP-20 WB

DATE 17 FEB 2016

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

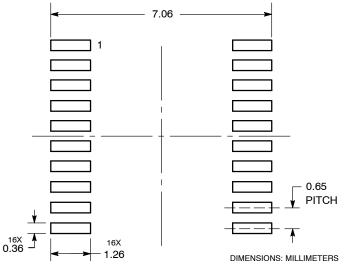
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- TERMINAL NOMBERS ARE SHOWN FOR REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0°	8°	0°	8°	

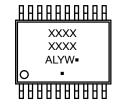
RECOMMENDED SOLDERING FOOTPRINT*

0.100 (0.004) -T- SEATING



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.

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